# Data Sheet

#### May 2, 2007

# High Performance Pin Driver

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The EL7156 high performance pin driver with three-state is suited to many ATE and level-shifting applications. The 3.5A peak drive capability makes this part an excellent choice when driving high capacitance loads.

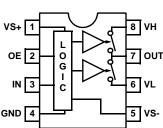
The output pin OUT is connected to input pins VH or VL respectively, depending on the status of the IN pin. When the OE pin is active low, the output is placed in the three-state mode. The isolation of the output FETs from the power supplies enables VH and VL to be set independently, enabling level-shifting to be implemented. Related to the EL7155, the EL7156 adds a lower supply pin VS- and makes VL an isolated and independent input. This feature adds applications flexibility and improves switching response due to the increased enhancement of the output FETs.

This pin driver has improved performance over existing pin drivers. It is specifically designed to operate at voltages down to 0V across the switch elements while maintaining good speed and ON-resistance characteristics.

Available in the 8 Ld SOIC and 8 Ld PDIP packages, the EL7156 is specified for operation over the full -40°C to +85°C temperature range.

### Pinout





#### Features

- Clocking speeds up to 40MHz
- 15ns t<sub>R</sub>/t<sub>F</sub>at 2000pF C<sub>LOAD</sub>
- 0.5ns rise and fall times mismatch
- 0.5ns t<sub>ON</sub>-t<sub>OFF</sub> prop delay mismatch
- 3.5pF typical input capacitance
- 3.5A peak drive
- Low ON-resistance of 3.5Ω
- · High capacitive drive capability
- Operates from 4.5V to 16.5V
- · Pb-free plus anneal available (RoHS compliant)

### Applications

- ATE/burn-in testers
- Level shifting
- IGBT drivers
- CCD drivers

### **Ordering Information**

PART NUMBER	PART MARKING	TAPE & REEL	PACKAGE	PKG. DWG. #
EL7156CN	EL7156CN	-	8 Ld PDIP	MDP0031
EL7156CNZ (Note)	EL7156CN Z	-	8 Ld PDIP* (Pb-free)	MDP0031
EL7156CS	7156CS	-	8 Ld SOIC	MDP0027
EL7156CS-T7	7156CS	7"	8 Ld SOIC	MDP0027
EL7156CS-T13	7156CS	13"	8 Ld SOIC	MDP0027
EL7156CSZ (Note)	7156CSZ	-	8 Ld SOIC (Pb-free)	MDP0027
EL7156CSZ-T7 (Note)	7156CSZ	7"	8 Ld SOIC (Pb-free)	MDP0027
EL7156CSZ-T13 (Note)	7156CSZ	13"	8 Ld SOIC (Pb-free)	MDP0027

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

\*Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in Reflow solder processing applications.

#### Absolute Maximum Ratings (T<sub>A</sub> = +25°C)

Supply Voltage (V <sub>S</sub> + to V <sub>S</sub> -)+18	V
Input Voltage	V
Continuous Output Current 200m	A
Storage Temperature Range65°C to +150°	С

#### **Thermal Information**

Ambient	Operatir	ng Ten	nper	ature .				40°C to	+85°C
Operating	g Junctio	on Ter	nper	ature .					+125°C
Power Di	ssipatio	n						see	curves
Pb-free r	eflow pro	ofile .						see link	below
http://w	/ww.inte	rsil.co	m/pl	ofree/P	b-Fr	eeReflow	.asp		
*Dh froo	PDIPs	can	be	used	for	through	hole	wave	solder
	PUIPe	can	pe	used	TOP	Inrough	nole	wave	solder

processing only. They are not intended for use in Reflow solder processing applications.

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typical values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore:  $T_J = T_C = T_A$ 

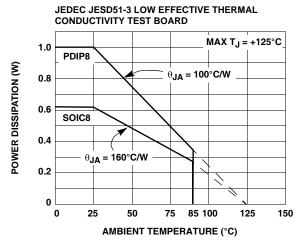
<b>Electrical Specifications</b>	$V_{S}$ + = +15V, $V_{H}$ = +15V, $V_{L}$ = 0V, $V_{S}$ - = 0V, $T_{A}$ = +25°C, unless otherwise specified.
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PARAMETER	DESCRIPTION	CONDITION	MIN	ТҮР	MAX	UNIT
INPUT						
V <sub>IH</sub>	Logic '1' Input Voltage		2.4			V
IIH	Logic '1' Input Current	$V_{IH} = V_S +$		0.1	10	μA
V <sub>IL</sub>	Logic '0' Input Voltage				0.8	V
۱ <sub>۱</sub>	Logic '0' Input Current	$V_{IL} = 0V$		0.1	10	μA
C <sub>IN</sub>	Input Capacitance			3.5		pF
R <sub>IN</sub>	Input Resistance			50		MΩ
OUTPUT				1	1	
R <sub>OVH</sub>	ON-Resistance V <sub>H</sub> to OUT	I <sub>OUT</sub> = -200 mA		2.7	4.5	Ω
R <sub>OVL</sub>	ON-Resistance V <sub>L</sub> to OUT	I <sub>OUT</sub> = +200 mA		3.5	5.5	Ω
IOUT	Output Leakage Current	$OE = 0V, OUT = V_H/V_L$		0.1	10	μA
I <sub>PK</sub>	Peak Output Current	Source		3.5		А
(linear resistive operation)	Sink		3.5		А	
IDC	Continuous Output Current	Source/Sink	200			mA
POWER SUPPL	Y					
I <sub>S</sub>	Power Supply Current	Inputs = $V_{S}$ +		1.3	3	mA
I <sub>VH</sub>	Off Leakage at $V_H$ and $V_L$	$V_{H}, V_{L} = 0V$		4	10	μA
SWITCHING CH	IARACTERISTICS		I	1	1	1
t <sub>R</sub>	Rise Time	C <sub>L</sub> = 2000pF		14.5		ns
t <sub>F</sub>	Fall Time	C <sub>L</sub> = 2000pF		15		ns
$t_{RF\Delta}$	t <sub>R</sub> , t <sub>F</sub> Mismatch	C <sub>L</sub> = 2000pF		0.5		ns
t <sub>d-1</sub>	Turn-Off Delay Time	C <sub>L</sub> = 2000pF		9.5		ns
t <sub>d-2</sub>	Turn-On Delay Time	C <sub>L</sub> = 2000pF		10		ns
$t_{d\Delta}$	t <sub>d-1</sub> -t <sub>d-2</sub> Mismatch	C <sub>L</sub> = 2000pF		0.5		ns
t <sub>d-3</sub>	Three-state Delay Enable			10		ns
t <sub>d-4</sub>	Three-state Delay Disable			10		ns

<b>Electrical Specifications</b> $V_S$ + = +5V, $V_H$ = +5V, $V_L$ = -5V, $V_S$ - = -5V, $T_A$ = +25°C, unless otherwise speci
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PARAMETER	DESCRIPTION CONDITION MIN		ТҮР	MAX	UNIT	
INPUT				1	1	I
V <sub>IH</sub>	Logic '1' Input Voltage		2.0			V
IIH	Logic '1' Input Current	$V_{IH} = V_S +$		0.1	10	μA
V <sub>IL</sub>	Logic '0' Input Voltage				0.8	V
IIL	Logic '0' Input Current	$V_{IL} = 0V$		0.1	10	μA
C <sub>IN</sub>	Input Capacitance			3.5		pF
R <sub>IN</sub>	Input Resistance			50		MΩ
OUTPUT			U			
R <sub>OVH</sub>	ON-Resistance V <sub>H</sub> to OUT	I <sub>OUT</sub> = -200mA		3.4	5	Ω
R <sub>OVL</sub>	ON-Resistance V <sub>L</sub> to OUT	I <sub>OUT</sub> = +200mA		4	6	Ω
IOUT	Output Leakage Current	$OE = 0V, OUT = V_H/V_L$		0.1	10	μA
I <sub>PK</sub>	Peak Output Current	Source		3.5		А
(linear resistive operation	(linear resistive operation)	Sink		3.5		А
IDC	Continuous Output Current	Source/Sink	200			mA
POWER SUPPLY	1		U			
I <sub>S</sub>	Power Supply Current	Inputs = $V_{S}$ +		1	2.5	mA
V <sub>H</sub>	Off Leakage at $V_H$ and $V_L$	$V_{H}, V_{L} = 0V$		4	10	μA
SWITCHING CH	ARACTERISTICS		U			
t <sub>R</sub>	Rise Time	C <sub>L</sub> = 2000pF		17		ns
tF	Fall Time	C <sub>L</sub> = 2000pF		17		ns
t <sub>RF</sub>	t <sub>R</sub> , t <sub>F</sub> Mismatch	C <sub>L</sub> = 2000pF		0		ns
t <sub>d-1</sub>	Turn-Off Delay Time	C <sub>L</sub> = 2000pF		11.5		ns
t <sub>d-2</sub>	Turn-On Delay Time	C <sub>L</sub> = 2000pF		12		ns
$t_{d\Delta}$	t <sub>d-1</sub> -t <sub>d-2</sub> Mismatch	C <sub>L</sub> = 2000pF		0.5		ns
t <sub>d-3</sub>	Three-state Delay Enable			10		ns
t <sub>d-4</sub>	Three-state Delay Disable			10		ns

### **Typical Performance Curves**





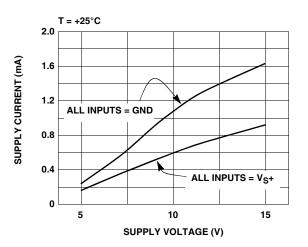


FIGURE 3. QUIESCENT SUPPLY CURRENT vs SUPPLY VOLTAGE

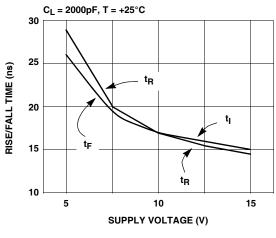


FIGURE 5. RISE/FALL TIME vs SUPPLY VOLTAGE

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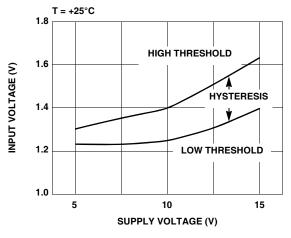


FIGURE 2. INPUT THRESHOLD vs SUPPLY VOLTAGE

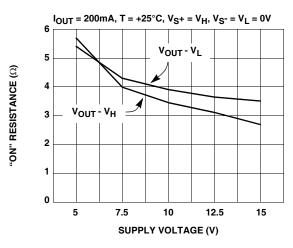


FIGURE 4. "ON"-RESISTANCE vs SUPPLY VOLTAGE

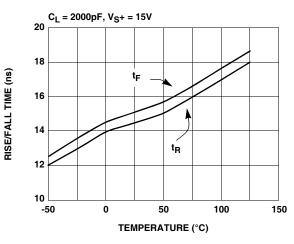


FIGURE 6. RISE/FALL TIME vs TEMPERATURE



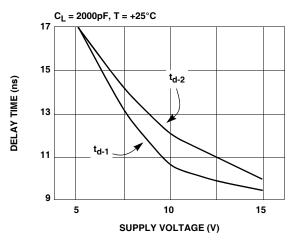


FIGURE 7. PROPAGATION DELAY vs SUPPLY VOLTAGE

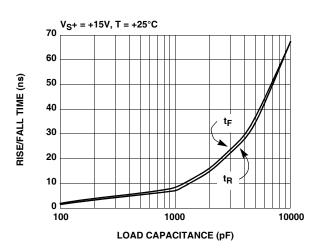


FIGURE 9. RISE/FALL TIME vs LOAD CAPACITANCE

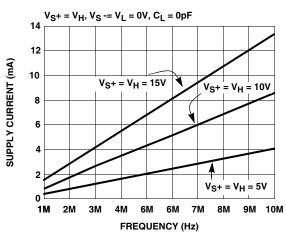


FIGURE 11. SUPPLY CURRENT vs FREQUENCY

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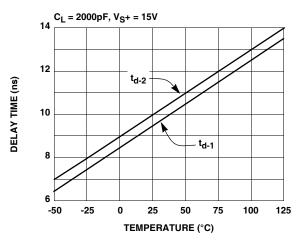


FIGURE 8. PROPAGATION DELAY vs TEMPERATURE

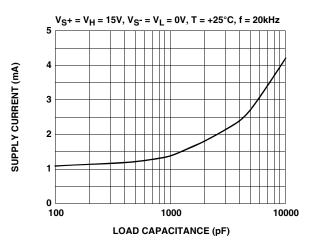


FIGURE 10. SUPPLY CURRENT vs LOAD CAPACITANCE

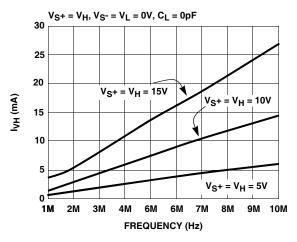


FIGURE 12. V<sub>H</sub> SUPPLY CURRENT vs FREQUENCY

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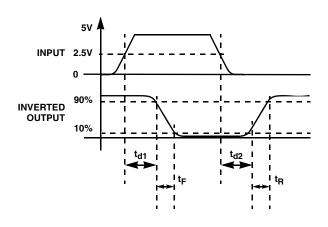
## Truth Table

OE	IN	OUT
0	0	Three-state
0	1	Three-state
1	0	V <sub>H</sub>
1	1	VL

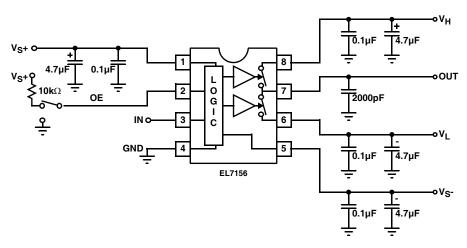
## **Operating Voltage Range**

PIN	MIN	MAX
V <sub>S</sub> - to GND	-5	0
V <sub>S</sub> + to V <sub>S</sub> -	5	16.5
$V_H$ to $V_L$	0	16.5
V <sub>S</sub> + to V <sub>H</sub>	0	16.5
V <sub>S</sub> + to GND	5	16.5
V <sub>L</sub> to V <sub>S</sub> -	0	16.5
Three-state Output	VL	V <sub>H</sub>

# Timing Diagram



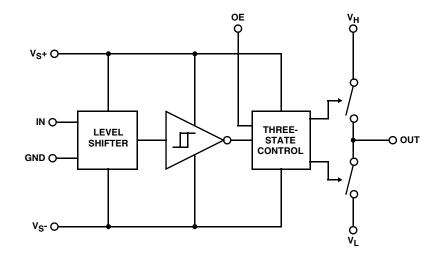
## Standard Test Configuration



## **Pin Descriptions**

PIN	NAME	FUNCTION	EQUIVALENT CIRCUIT
1	VS+	Positive Supply Voltage	
2	OE	Output Enable	
3	IN	Input	Reference Circuit 1
4	GND	Ground	
5	VS-	Negative Supply Voltage	
6	VL	Lower Output Voltage	
7	OUT	Output	V <sub>H</sub> V <sub>S</sub> -o-j-lo V <sub>S</sub> - V <sub>V</sub> - V V V V V V V V V V V V V V V V V V
8	VH	High Output Voltage	

## Block Diagram



### Applications Information

#### **Product Description**

The EL7156 is a high performance 40MHz pin driver. It contains two analog switches connecting VH and VL to OUT. Depending on the value of the IN pin, one of the two switches will be closed and the other switch open. An output enable (OE) is also supplied which opens both switches simultaneously.

Due to the topology of the EL7156, both the VH and VL pins can be connected to any voltage between the VS+ and VSpins, but VH must be greater than VL in order to prevent turning on the body diode at the output stage.

The EL7156 is available in both the 8 Ld SOIC and the 8 Ld PDIP packages. The relevant package should be chosen depending on the calculated power dissipation.

### Three-state Operation

When the OE pin is low, the output is three-state (floating). The output voltage is the parasitic capacitance's voltage. It can be any voltage between VH and VL, depending on the previous state. At three-state, the output voltage can be pushed to any voltage between VH and VL. The output voltage can't be pushed higher than VH or lower than VL since the body diode at the output stage will turn on.

### Supply Voltage Range and Input Compatibility

The EL7156 is designed for operation on supplies from 5V to 15V (4.5V to 16.5V maximum). "Operating Voltage Range" on page 6 shows the specifications for the relationship between the VS+, VS-, VH, VL, and GND pins.

All input pins are compatible with both 3V and 5V CMOS signals. With a positive supply (V<sub>S</sub>+) of 5V, the EL7156 is also compatible with TTL inputs.

### Power Supply Bypassing

When using the EL7156, it is very important to use adequate power supply bypassing. The high switching currents developed by the EL7156 necessitate the use of a bypass capacitor between the supplies (VS+ and VS-) and GND pins. It is recommended that a 2.2 $\mu$ F tantalum capacitor be used in parallel with a 0.1 $\mu$ F low-inductance ceramic MLC capacitor. These should be placed as close to the supply pins as possible. It is also recommended that the VH and VL pins have some level of bypassing, especially if the EL7156 is driving highly capacitive loads.

### Power Dissipation Calculation

When switching at high speeds, or driving heavy loads, the EL7156 drive capability is limited by the rise in die temperature brought about by internal power dissipation. For reliable operation, die temperature must be kept below  $T_{JMAX}$  (+125°C). It is necessary to calculate the power dissipation for a given application prior to selecting the package type.

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Power dissipation may be calculated:

$$PD = (V_{S} \times I_{S}) + (C_{VS} \times V_{S}^{2} \times f) + [(C_{INT} + C_{L}) \times V_{OUT}^{2} \times f]$$
(EQ. 1)

where:

 $\mathsf{V}_S$  is the total power supply to the EL7156 (from  $\mathsf{V}_S\text{+}$  to GND)

 $V_{\mbox{OUT}}$  is the swing on the output (V\_H to V\_L)

 $C_{VS}$  is the integral capacitance due to  $V_S\mbox{+}$ 

 $C_{INT}$  is the integral load capacitance due to  $V_H$ 

 $I_S$  is the quiescent supply current (3mA max)

f is frequency

TABLE 1.	INTEGRAL	CAPACITANCE

$V_{S}$ + = $V_{H}(V)$	C <sub>VS</sub> (pF)	C <sub>INT</sub> (pF)
5	80	120
10	85	145
15	90	180

Having obtained the application's power dissipation, a maximum package thermal coefficient may be determined, to maintain the internal die temperature below  $T_{JMAX}$ :

$$\theta_{JA} = \frac{T_{JMAX} - T_{MAX}}{PD}$$
(EQ. 2)

where:

T<sub>JMAX</sub> is the maximum junction temperature (+125°C)

T<sub>MAX</sub> is the maximum operating temperature

PD is the power dissipation calculated above

 $\theta_{\mbox{JA}}$  thermal resistance on junction to ambient

 $\theta_{JA}$  is 160°C/W for the SOIC8 package and 100°C/W for the PDIP8 package when using a standard JEDEC JESD51-3 single-layer test board. If  $T_{JMAX}$  is greater than +125°C when calculated using Equation 2, then one of the following actions must be taken:

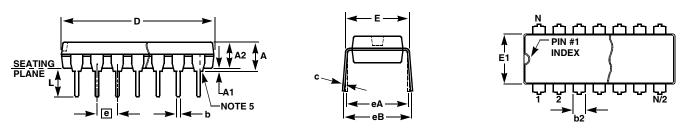
Reduce  $\theta_{JA}$  the system by designing more heat-sinking into the PCB (as compared to the standard JEDEC JESD51-3).

Use the PDIP8 instead of the SOIC8 package.

De-rate the application either by reducing the switching frequency, the capacitive load, or the maximum operating (ambient) temperature ( $T_{MAX}$ ).

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### Plastic Dual-In-Line Packages (PDIP)



#### MDP0031 PLASTIC DUAL-IN-LINE PACKAGE

SYMBOL	PDIP8	PDIP14	PDIP16	PDIP18	PDIP20	TOLERANCE	NOTES
А	0.210	0.210	0.210	0.210	0.210	MAX	
A1	0.015	0.015	0.015	0.015	0.015	MIN	
A2	0.130	0.130	0.130	0.130	0.130	±0.005	
b	0.018	0.018	0.018	0.018	0.018	±0.002	
b2	0.060	0.060	0.060	0.060	0.060	+0.010/-0.015	
С	0.010	0.010	0.010	0.010	0.010	+0.004/-0.002	
D	0.375	0.750	0.750	0.890	1.020	±0.010	1
E	0.310	0.310	0.310	0.310	0.310	+0.015/-0.010	
E1	0.250	0.250	0.250	0.250	0.250	±0.005	2
е	0.100	0.100	0.100	0.100	0.100	Basic	
eA	0.300	0.300	0.300	0.300	0.300	Basic	
eB	0.345	0.345	0.345	0.345	0.345	±0.025	
L	0.125	0.125	0.125	0.125	0.125	±0.010	
Ν	8	14	16	18	20	Reference	

NOTES:

- 1. Plastic or metal protrusions of 0.010" maximum per side are not included.
- 2. Plastic interlead protrusions of 0.010" maximum per side are not included.
- 3. Dimensions E and eA are measured with the leads constrained perpendicular to the seating plane.
- 4. Dimension eB is measured with the lead tips unconstrained.
- 5. 8 and 16 lead packages have half end-leads as shown.

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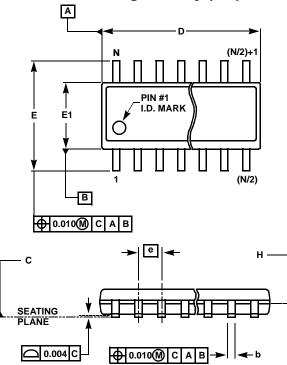
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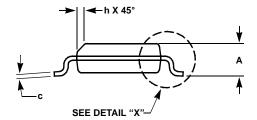
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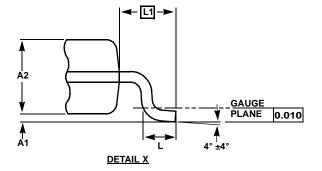


Rev. C 2/07

Small Outline Package Family (SO)







### MDP0027

SMALL OUTLINE PACKAGE FAMILY (SO)

SYMBOL	SO-8	SO-14	SO16 (0.150")	SO16 (0.300") (SOL-16)	SO20 (SOL-20)	SO24 (SOL-24)	SO28 (SOL-28)	TOLERANCE	NOTES
А	0.068	0.068	0.068	0.104	0.104	0.104	0.104	MAX	-
A1	0.006	0.006	0.006	0.007	0.007	0.007	0.007	±0.003	-
A2	0.057	0.057	0.057	0.092	0.092	0.092	0.092	±0.002	-
b	0.017	0.017	0.017	0.017	0.017	0.017	0.017	±0.003	-
С	0.009	0.009	0.009	0.011	0.011	0.011	0.011	±0.001	-
D	0.193	0.341	0.390	0.406	0.504	0.606	0.704	±0.004	1, 3
Е	0.236	0.236	0.236	0.406	0.406	0.406	0.406	±0.008	-
E1	0.154	0.154	0.154	0.295	0.295	0.295	0.295	±0.004	2, 3
е	0.050	0.050	0.050	0.050	0.050	0.050	0.050	Basic	-
L	0.025	0.025	0.025	0.030	0.030	0.030	0.030	±0.009	-
L1	0.041	0.041	0.041	0.056	0.056	0.056	0.056	Basic	-
h	0.013	0.013	0.013	0.020	0.020	0.020	0.020	Reference	-
Ν	8	14	16	16	20	24	28	Reference	-

Rev. M 2/07

NOTES:

- 1. Plastic or metal protrusions of 0.006" maximum per side are not included.
- 2. Plastic interlead protrusions of 0.010" maximum per side are not included.
- 3. Dimensions "D" and "E1" are measured at Datum Plane "H".

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4. Dimensioning and tolerancing per ASME Y14.5M-1994